

IMFEDK 2025

Time	Nov 13, 2025 (THU)		Nov 14, 2025 (FRI)	
9 0 5 10 15 20 25 30 35 40 45 50 55				
			9:30-10:10 Session 4 Sensor Chair:	9:30-10:10 IN04 (Invited) (tentative)Flexible Hybrid Electronics for Sensing Applications Joseph Andrews (Univ. Wisconsin- Madison)
10 0 5 10 15 20 25 30 35 40 45 50 55	10:00-10:10 Opening Remarks		10:10-10:20 Break	
	10:10-10:50 Poster Short Presentation Chair: TBA	10:10-10:50 Poster Short Presentation (2min x 19)	10:20-12:00 Poster Viewing Session	
	10:50-11:00 Break			
11 0 5 10 15 20 25 30 35 40 45 50 55	11:00-11:40 Keynote Speech Chair:	11:00-11:40 KS01 -Keynote Speech- Polarization inverted ScAlN piezoelectric multilayer RF filters Takahiro Yanagitani (Waseda Univ.)	12:00-13:00 Lunch	
12 0 5 10 15 20 25 30 35 40 45 50 55	11:40-13:00 Lunch			
13 0 5 10 15 20 25 30 35 40 45 50 55	13:00-14:00 Session 1 Characterization Chair: TBA	13:00-13:40 IN01 (Invited) Imaging electrons, holes, and the depletion layer in semiconductor devices by operando photoemission electron microscopy Keiki Fukumoto (KEK) 13:40-14:00 Impact of Probe-Induced Thermal Flow in Cryogenic I- V Measurement of Power Devices with Kelvin Connection	13:00-14:40 Session 5 Integrated Circuits Chair:	13:00-13:40 IN05 (Invited) Challenges and Opportunities of Oxide-semiconductor Channel Transistor DRAM (OCTRAM) Shoichi Kabuyanagi (KIOXIA)
	14:00-14:20 Break			13:40-14:00 Cross-coupled Voltage Doubler with Improved Subthreshold Performance 14:00-14:20 CMOS Image Sensor Pixels Capable of Extracting Two-Dimensional Edge
14 0 5 10 15 20 25 30 35 40 45 50 55	14:20-15:40 Session 2 Process and Device Technology Chair:	14:20-15:00 IN02 (Invited) Epitaxial graphene on SiC Wataru Norimatsu (Waseda Univ.)	14:20-14:40 Low-Noise Reset Transistor for LOIC CMOS Image Sensors Using a Two-Step Reset Scheme	14:40-15:00 Break
		15:00-15:20 Enhanced Electrical Performance of Recessed-Gate GaN MIS-HEMTs Via Complete Barrier Removal and Regrowth of AlN/AlGaN Barrier 15:20-15:40 R04-fabrication and Characterization of ZrO2/AlGaN/GaN MIS-HEMTs with ex-situ AlN cap Layer		
15 0 5 10 15 20 25 30 35 40 45 50 55	15:40-16:00 Break		15:00-16:20 Special Lecture Emerging Widebandgap Devices Chair:	15:00-15:40 IN06 (Invited) Mobility and High-Reliability Oxide Semiconductor Thin-Film Transistors Yusaku Magari (Kochi Univ. of Tech.)
				15:40-16:20 IN07 (Invited) Recent advances in research and development to realize inch-sized homoepitaxial diamond wafers Hideaki Yamada (AIST)
16 0 5 10 15 20 25 30 35 40 45 50 55	16:00-17:20 Session 3 Process and Characterization Chair:	16:00-16:40 (Invited) IN03 Novel crystallographic etching of β -Ga2O3 Takayoshi Oshima (NIMS)	16:20-16:40 Break (Award Assessments)	
		16:40-17:00 Measurement of the Electrical Properties of Ti407 Produced by Surface Oxide Film Stripping /Transfer Method of Liquid Metal Alloys	16:40-17:00 Award Presentation	
17 0 5 10 15 20 25 30 35 40 45 50 55	17:00-17:20 Anodization of each individual titanium microwires on a chip under different conditions		17:00-17:10 Closing Remarks	
	Commemorative group photo with all participants			
18 0 5 10 15 20 25 30 35 40 45 50 55	18:00-19:30 Banquet (1F in Jojukan)			